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FORM PTO-1449

U.S. Department of Commerce  
Patent and Trademark Office

Atty. Docket No.  
FIS920030241US1

Application No.  
10/689,506

INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT

(Use several sheets if necessary)

Applicant  
Haujie CHEN et al.

Filing Date  
October 20, 2003

Group  
2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER							DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>JMK</i>	2005	0	0	3	5	4	7	0	02-17-05	KO et al.	-	-	
<i>JMK</i>	2004	0	1	7	3	8	1	5	09-09-04	YEO et al.	-	-	
<i>JMK</i>	2005	0	0	5	1	8	5	1	03-10-05	CHEN et al.	-	-	
		6	8	1	9	1	9	2	05-10-05	CHEN et al.	-	-	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>JMK</i>		Search Reporting and Written Opinion for PCT/US04/34562, dated March 15, 2007.

EXAMINER

*[Signature]*

DATE CONSIDERED

6/22/07

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5/18/06

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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use several sheets if necessary)				Applicant Huajie CHEN, et al..			
				Filing Date 10/20/2003		Group 2813	
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